

YJ Planar Schottky Barrier Diode Die Specification

100V 10A, 87mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB087S100AS-280A

Main Products Characterstics

Maximum Ratings

Symbol	Value
I_F	10A
V_R	100V
T_J	175°C
T_{stg}	250°C
t_{stg}	1000h

Static Electrical Characteristics (Ta = 25°C)

Symbol	Value
I_F	10A
V_F	≤ 2%
I_{RRM}	10A
V_{RRM}	100V
I_{FSM}	10A
V_{FSM}	100V
I_{TSM}	10A
V_{TSM}	100V
I_{TSM}	10A
V_{TSM}	100V

Device Schematics and Outline Drawing

Die Thickness *	
Die Size **	
Top Metal Pad	
Active Area	
Top Metal	
Back Metal	
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.